

Hasan HÃ¼seyin GÃ¼llÃ¼

List of Publications by Year in descending order

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papers

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516561

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docs citations

73
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503
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of TiO ₂ Thin Film with Different Dopants in Bringing Au-Metal into a Contact with n-Si. Journal of Inorganic and Organometallic Polymers and Materials, 2022, 32, 1067-1077.	1.9	5
2	Temperature-dependent optical characteristics of sputtered Ga-doped ZnO thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 263, 114834.	1.7	9
3	Temperature effects on optical characteristics of CdSe thin films. Materials Science in Semiconductor Processing, 2021, 123, 105559.	1.9	7
4	Optical and Nanomechanical Properties of Ga ₂ Se ₃ Single Crystals and Thin Films. Jom, 2021, 73, 558-565.	0.9	2
5	Improvement of electrical characteristics of SnSe/Si heterostructure by integration of Si nanowires. Physica B: Condensed Matter, 2021, 604, 412669.	1.3	4
6	Capacitance, conductance, and dielectric characteristics of Al/TiO ₂ /Si diode. Journal of Materials Science: Materials in Electronics, 2021, 32, 13549-13567.	1.1	14
7	Fabrication of CdSexTe1-x thin films by sequential growth using double sources. Physica B: Condensed Matter, 2021, 619, 413232.	1.3	2
8	INVESTIGATION OF CONDUCTIVITY CHARACTERISTICS OF Znâ€“Inâ€“Se THIN FILMS. Surface Review and Letters, 2020, 27, 1950083.	0.5	2
9	Synthesis and temperature-tuned band gap characteristics of magnetron sputtered ZnTe thin films. Physica B: Condensed Matter, 2020, 582, 411968.	1.3	18
10	Material and device properties of Si-based Cu _{0.5} Ag _{0.5} InSe ₂ thin-film heterojunction diode. Journal of Materials Science: Materials in Electronics, 2020, 31, 1566-1573.	1.1	2
11	Dark and illuminated electrical characteristics of Si-based photodiode interlayered with CuCo ₅ S ₈ nanocrystals. Journal of Materials Science: Materials in Electronics, 2020, 31, 935-948.	1.1	24
12	Electrical characteristics of organic heterojunction with an alternating benzotriazole and fluorene containing copolymer. Journal of Materials Science: Materials in Electronics, 2020, 31, 18816-18831.	1.1	12
13	Electrical characterization of CdZnTe/Si diode structure. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	9
14	Analysis of temperature-dependent forward and leakage conduction mechanisms in organic thin film heterojunction diode with fluorine-based PCBM blend. Journal of Materials Science: Materials in Electronics, 2020, 31, 15233-15242.	1.1	9
15	First-principles studies of Tin+1SiNn (nâ€“=â€“1, 2, 3) MAX phase. Philosophical Magazine, 2020, 100, 2183-2204.	1.1	4
16	Material and Si-based diode analyses of sputtered ZnTe thin films. Journal of Materials Science: Materials in Electronics, 2020, 31, 11390-11397.	1.1	5
17	Frequency effect on electrical and dielectric characteristics of HfO ₂ -interlayered Si-based Schottky barrier diode. Journal of Materials Science: Materials in Electronics, 2020, 31, 9394-9407.	1.1	21
18	Investigation of band gap energy versus temperature for SnS ₂ thin films grown by RF-magnetron sputtering. Physica B: Condensed Matter, 2020, 591, 412264.	1.3	8

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19	Influence of temperature on optical properties of electron-beam-evaporated ZnSe thin film. <i>Physica Scripta</i> , 2020, 95, 075804.	1.2	5
20	Temperature-dependent material characterization of CuZnSe ₂ thin films. <i>Thin Solid Films</i> , 2020, 701, 137941.	0.8	3
21	Investigation of structural, electronic, magnetic and lattice dynamical properties for XCoBi (X: Ti, Zr, Tj) ETQq1 1 0.784314 rgBT /Over	1.3	38
22	Electrical properties of Al/PCBM:ZnO/p-Si heterojunction for photodiode application. <i>Journal of Alloys and Compounds</i> , 2020, 827, 154279.	2.8	61
23	Temperature-dependent optical and electrical characterization of Cu-Ga-S thin films and their diode characteristics on n-Si. <i>Optik</i> , 2020, 208, 164485.	1.4	1
24	Temperature and frequency effects on electrical and dielectric properties of n-4H SiC based metal-insulator-semiconductor (MIS) diode interlayered with Si ₃ N ₄ thin film. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 8705-8717.	1.1	23
25	FABRICATION AND CHARACTERIZATION OF TiO ₂ THIN FILM FOR DEVICE APPLICATIONS. <i>Surface Review and Letters</i> , 2019, 26, 1850205.	0.5	3
26	Investigation of electrical characteristics of Ag/ZnO/Si sandwich structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 15371-15378.	1.1	12
27	First principles study on the structural, electronic, mechanical and lattice dynamical properties of XRhSb (X = Ti and Zr) paramagnet half-Heusler antimonides. <i>Materials Research Express</i> , 2019, 6, 106315.	0.8	17
28	Analysis of forward and reverse biased current-voltage characteristics of Al/Al ₂ O ₃ /n-Si Schottky diode with atomic layer deposited Al ₂ O ₃ thin film interlayer. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 19383-19393.	1.1	27
29	Effects of Si nanowire on the device properties of n-ZnSe/p-Si heterostructure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 4760-4765.	1.1	8
30	Determination of current transport characteristics in Au-Cu/CuO/n-Si Schottky diodes. <i>Physica B: Condensed Matter</i> , 2019, 570, 246-253.	1.3	20
31	CZTSSe thin films fabricated by single step deposition for superstrate solar cell applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 11301-11306.	1.1	8
32	Investigation of electrical properties of $\text{In/ZnIn}_2\text{Te}_4/\text{n-Si/Ag}$ diode. <i>Bulletin of Materials Science</i> , 2019, 42, 1.	0.8	9
33	Analysis of temperature-dependent transmittance spectra of Zn _{0.5} In _{0.5} Se (ZIS) thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 9356-9362.	1.1	0
34	Frequency effect on electrical and dielectric characteristics of In/Cu ₂ ZnSnTe ₄ /Si/Ag diode structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 9814-9821.	1.1	11
35	Optical band gap and dispersion of optical constants of Cu-Ga-S thin films. <i>Optik</i> , 2019, 186, 147-154.	1.4	8
36	Temperature dependence of band gaps in sputtered SnSe thin films. <i>Journal of Physics and Chemistry of Solids</i> , 2019, 131, 22-26.	1.9	18

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37	Electrical Characterization of ZnInSe ₂ /Cu _{0.5} Ag _{0.5} InSe ₂ Thin-Film Heterojunction. Journal of Electronic Materials, 2019, 48, 3096-3104.	1.0	3
38	Temperature dependence of electrical properties in $\text{In/Cu}_2\text{ZnSnTe}_4/\text{Si/Ag}$ diodes. Bulletin of Materials Science, 2019, 42, 1.	0.8	13
39	Construction of self-assembled vertical nanoflakes on CZTSSe thin films. Materials Research Express, 2019, 6, 026421.	0.8	8
40	Structural and temperature-dependent optical properties of thermally evaporated CdS thin films. Materials Science in Semiconductor Processing, 2019, 93, 148-152.	1.9	37
41	Material characterization of thermally evaporated ZnSn ₂ Te ₄ thin films. Optik, 2019, 178, 45-50.	1.4	1
42	Analysis of current conduction mechanism in CZTSSe/n-Si structure. Journal of Materials Science: Materials in Electronics, 2018, 29, 5264-5274.	1.1	20
43	Investigation of carrier transport mechanisms in the Cuâ€Znâ€Se based hetero-structure grown by sputtering technique. Canadian Journal of Physics, 2018, 96, 816-825.	0.4	10
44	Temperature-Dependent Electrical Characteristics of Au/Si ₃ N ₄ /4H n-SiC MIS Diode. Journal of Electronic Materials, 2018, 47, 2979-2987.	1.0	24
45	INVESTIGATION ON DEVICE CHARACTERISTICS OF n-CdS/p-Ag(Ga-In)Te ₂ HETEROJUNCTION DIODE. Surface Review and Letters, 2018, 25, 1850107.	0.5	1
46	Temperature dependence of electrical properties in Cu _{0.5} Ag _{0.5} InSe ₂ /Si heterostructure. Journal of Materials Science: Materials in Electronics, 2018, 29, 11258-11264.	1.1	5
47	Structural and optical properties of thermally evaporated Cu-Ga-S (CGS) thin films. Physica B: Condensed Matter, 2018, 547, 92-96.	1.3	4
48	Annealing Effect on Dark Electrical Conductivity and Photoconductivity of Ga-In-Se Thin Films. Acta Physica Polonica A, 2018, 133, 1119-1124.	0.2	0
49	Structural characterization of Znâ€Inâ€Se thin films. Modern Physics Letters B, 2017, 31, 1750043.	1.0	6
50	Deposition of CZTSe thin films and illumination effects on the device properties of Ag/n-Si/p-CZTSe/In heterostructure. Journal of Alloys and Compounds, 2017, 709, 337-343.	2.8	16
51	Investigation of precursor sequence and post-annealing effects on the properties of Cu ₂ SnZnSe ₄ thin films deposited by the elemental thermal evaporation. Materials Research Express, 2017, 4, 086411.	0.8	12
52	Study on the electrical properties of ZnSe/Si heterojunction diode. Journal of Materials Science: Materials in Electronics, 2017, 28, 17806-17815.	1.1	26
53	Optical and electrical characteristics of thermally evaporated Cu _{0.5} Ag _{0.5} InSe ₂ thin films. Thin Solid Films, 2017, 639, 29-35.	0.8	11
54	Investigations of thermal annealing role on the optical properties of Zn-In-Se thin films. Optik, 2017, 144, 603-612.	1.4	7

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55	Investigation of post-thermal annealing on material properties of CuInZnSe thin films. Journal of Semiconductors, 2017, 38, 123001.	2.0	1
56	Device Characterization of ZnInSe ₂ Thin Films. Energy Procedia, 2016, 102, 110-120.	1.8	8
57	Structural characteristics of thermally evaporated Cu _{0.5} Ag _{0.5} InSe ₂ thin films. Materials Research Express, 2016, 3, 055901.	0.8	7
58	Investigation of optical parameters of thermally evaporated ZnSe thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1224-1228.	0.8	4
59	Investigation of structural and optical parameters of CuAgInSe thin films deposited by thermal evaporation method. Optik, 2015, 126, 1578-1583.	1.4	5
60	Device behavior of an In/p-Ag(Ga,In)Te ₂ /n-Si/Ag heterojunction diode. Materials Science in Semiconductor Processing, 2015, 34, 138-145.	1.9	26
61	Study on the Structural and Electrical Properties of Sequentially Deposited AgGaInTe Thin Films. Journal of Low Temperature Physics, 2015, 178, 162-173.	0.6	4
62	Enhanced diode performance in cadmium telluride-silicon nanowire heterostructures. Journal of Alloys and Compounds, 2015, 644, 131-139.	2.8	16
63	Improved diode properties in zinc telluride thin film-silicon nanowire heterojunctions. Philosophical Magazine, 2015, 95, 1164-1183.	0.7	12
64	Device application of AgGa _{0.5} In _{0.5} Se ₂ thin films deposited by thermal sequential stacked layer method. Materials Research Express, 2014, 1, 046407.	0.8	2
65	Structural and optical properties of thermally evaporated GaInSe thin films. Modern Physics Letters B, 2014, 28, 1450101.	1.0	0
66	Characterization of Co-evaporated Cu-Ag-In-Se Thin Films. Brazilian Journal of Physics, 2014, 44, 719-725.	0.7	5
67	Structural and optical properties of ZnInTe thin films deposited by thermal evaporation technique. Journal of Alloys and Compounds, 2013, 566, 83-89.	2.8	10
68	Influence of the spot size of the probe beam on the detected THz power using electro-optic detection method. , 2009, , .		0
69	THz probe studies of MBE grown epitaxial GaAs. Journal of Physics: Conference Series, 2009, 193, 012088.	0.3	4
70	Enhancement in Photovoltaic Characteristics of CdS/CdTe Heterojunction. Journal of Polytechnic, 0, , 801-805.	0.4	2
71	The Analysis of Inhomogeneous Barrier Height in In/SnTe/Si/Ag Diode. Journal of Polytechnic, 0, , .	0.4	0
72	Frequency Dependent Dielectric Properties of ZnSe/p-Si Diode. Journal of Polytechnic, 0, , .	0.4	0